

Si PNP TRANSISTOR

2SA573, 2SA574

EPOXY MOLDED, AUDIO AMP., RF AMP., SWITCHING

ABSOLUTE MAXIMUM RATINGS (Ta : 25°C)

		2SA573	2SA574	
COLLECTOR-BASE VOLTAGE	V _{CB0}	-30	-60	V
COLLECTOR-EMITTER VOLTAGE	V _{CE0}	-25	-50	V
EMITTER-BASE VOLTAGE	V _{EB0}	-5	-5	V
COLLECTOR CURRENT	I _C	-100	-100	mA
POWER DISSIPATION	P _C	300	300	mW
JUNCTION TEMPERATURE	T _J	125	125	°C
STORAGE TEMPERATURE	T _{stg}	-55~+125	-55~+125	°C

ELECTRICAL CHARACTERISTICS (Ta : 25°C)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
COLLECTOR CUTOFF CURRENT	I _{CB0}	V _{CB} : -20V, I _E : 0			-100	nA
STATIC FWD. CUR. TRANSFER RATIO	h _{FE}	V _{CE} : -6V, I _C : -1mA, NOTE 1	30		800	
TRANSITION FREQUENCY	f _T	V _{CE} : -10V, I _E : 2mA	80	150		MHz
COLLECTOR OUTPUT CAPACITANCE	C _{ob}	V _{CB} : -10V, I _E : 0, f : 1MHz		4	10	pF
BASE-COLLECTOR TIME CONSTANT	C _{eT_b'b}	V _{CB} : -10V, I _E : 2mA, f : 31.9MHz		50	150	ps
COLLECTOR-EMITTER SATURATION VOLTAGE	V _{CE(sat)}	I _C : -50mA, I _B : -10mA			-0.3	V
BASE-EMITTER SATURATION VOLTAGE	V _{BE(sat)}	I _C : -50mA, I _B : -10mA			-1.0	V

NOTE 1 : ACCORDING TO THE VALUE OF h_{FE}, THE DEVICES ARE CLASSIFIED AS FOLLOWS.

- RANK 1 : 30~70
- RANK 2 : 60~120
- RANK 3 : 90~180
- RANK 4 : 150~350
- RANK 5 : 250~500
- RANK 6 : 400~800

NOTE 2 : FOR COMPLEMENTARY CIRCUITS USING 2SA573 AND 2SA574, NPN DEVICES TYPE 2SC950 AND 2SC951 ARE RESPECTIVELY AVAILABLE FOR REQUEST.

